

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 4590-410		U.S. PATENT APPLICATION NO. 10/536,696	
				APPLICANT Arnaud GRISARD et al.			
				FILING DATE May 27, 2005		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
/J.R./	5,349,466	09-20-1994	Delacourt , et al.				
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
/J.R./	Christopher B. Ebert, Loren A. Eyres, Martin M. Fejer, James S. Harris, Jr. "MBE growth of antiphase GaAs films using GaAs/Ge/GaAs heteroepitaxy" Journal of Crystal Growth 201/202 (1888) 187-193						
EXAMINER /Joshel Rivera/				DATE CONSIDERED 11/18/2009			

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.